

GaAs: electro-optic coefficient

Semiconductors - New Data and Updates for several III-V (including mixed crystals) and II-VI Compounds

substance:	gallium arsenide (GaAs)
property:	electro-optic coefficient (optical properties)

electro-optic coefficient

For the electro-optic coefficient d_{14} measured by means of reflectance anisotropy spectroscopy at $T = 300$ K, see Fig. 1 [10P].

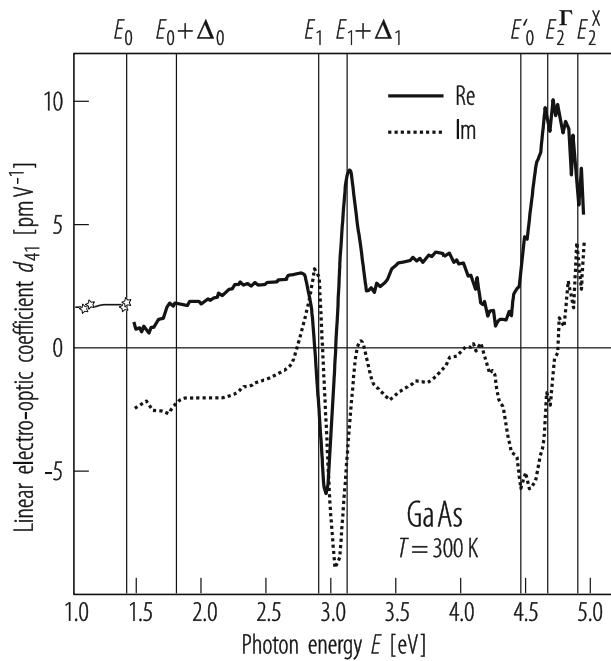


Fig. 1 GaAs. Real (full line) and imaginary (dashed line) electro-optic coefficient (d_{14}) for GaAs at room temperature [10P]. The values below the band gap (star symbols) are taken from ref. [92B]. The vertical lines indicate the energy of critical points.

References

- 92B Berseth, C.-A., Wuethrich, C., Reinhardt, F.K.: J. Appl. Phys. **71** (1992) 2821.
 10P Pristovsek, M.: Phys. Status Solidi B **247** (2010) 1974.